# Silicon PNP Power Transistors 2SA766

## DESCRIPTION

- With TO-66 package
- High power dissipation
- Complement to type 2SC1450

## APPLICATIONS

- Line-operated vertical deflection output
- Medium power amplifier

**PINNING(see Fig.2)**

| PIN | DESCRIPTION |
|---|---|
| 1 | Base |
| 2 | Emitter |
| 3 | Collector |


**Fig.1 simplified outline (TO-66) and symbol**

**Absolute maximum ratings(Ta=℃)**

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|---|---|---|---|---|
| $V_{CBO}$ | Collector-base voltage | Open emitter | -150 | V |
| $V_{CEO}$ | Collector-emitter voltage | Open base | -150 | V |
| $V_{EBO}$ | Emitter-base voltage | Open collector | -5 | V |
| $I_C$ | Collector current | | -0.4 | A |
| $I_{CM}$ | Collector current-peak | | -1.2 | A |
| $P_C$ | Collector power dissipation | $T_C \leq 80℃$ | 20 | W |
| $T_j$ | Junction temperature | | 150 | ℃ |
| $T_{stg}$ | Storage temperature | | -65~150 | ℃ |

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## CHARACTERISTICS

**Tj=25℃ unless otherwise specified**

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|---|---|---|---|---|---|---|
| $V_{CEO(SUS)}$ | Collector-emitter sustaining voltage | $I_C$=-0.2A ;L=25mH,$R_{BE}$=5kΩ | -150 | | | V |
| $V_{(BR)EBO}$ | Emitter-base breakdown voltage | $I_E$=-1mA ;$I_C$=0 | -5 | | | V |
| $V_{CEsat}$ | Collector-emitter saturation voltage | $I_C$=-1A; $I_B$=-0.1A | | | -1.0 | V |
| $V_{BE-1}$ | Base-emitter saturation voltage | $I_C$=-0.1A ; $V_{CE}$=-5V | | | -0.8 | V |
| $V_{BE-2}$ | Base-emitter saturation voltage | $I_C$=-0.5A ; $V_{CE}$=-5V | | | -1.0 | V |
| $I_{CBO}$ | Collector cut-off current | $V_{CB}$=-60V; $I_E$=0 | | | -30 | μA |
| $h_{FE-1}$ | DC current gain | $I_C$=-0.1A ; $V_{CE}$=-5V | 35 | | 150 | |
| $h_{FE-2}$ | DC current gain | $I_C$=-0.5A ; $V_{CE}$=-5V | 35 | | | |
| $f_T$ | Transition frequency | $I_E$=0.1A ; $V_{CB}$=-10V | | 15 | | MHz |

**PACKAGE OUTLINE**

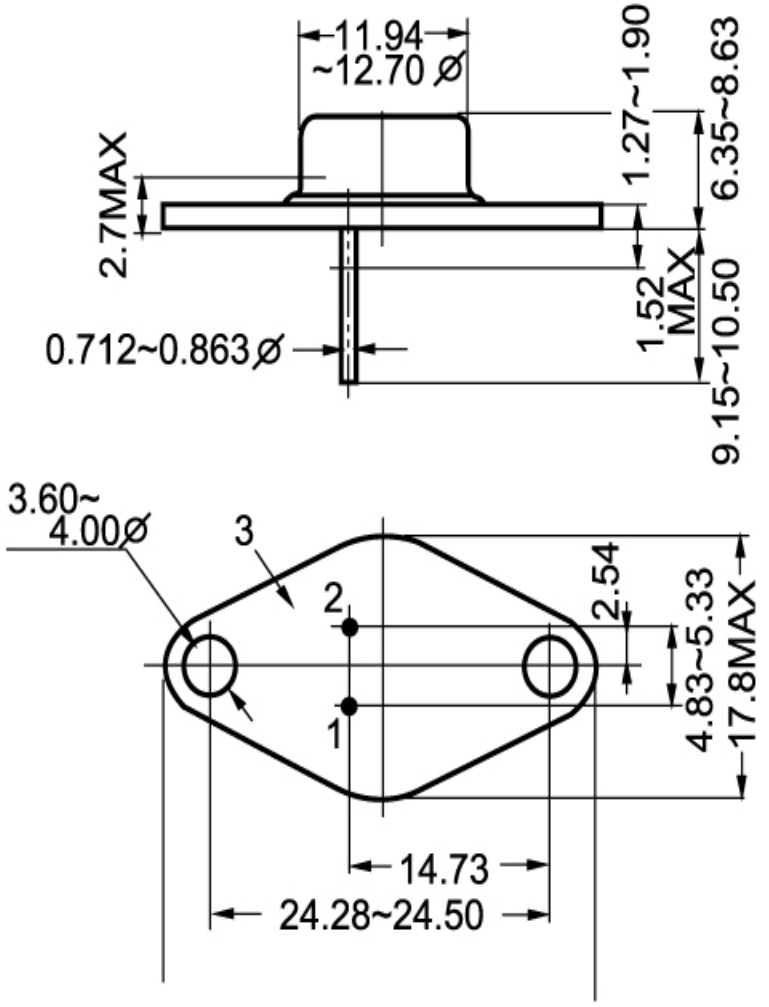


**Fig.2 outline dimensions**